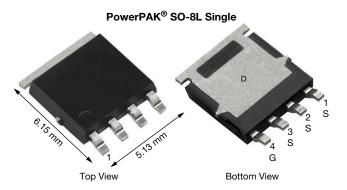
### SQJA82EP

www.vishay.com

**Vishay Siliconix** 

# Automotive N-Channel 80 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY	
V <sub>DS</sub> (V)	80
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS}$ = 10 V	0.0082
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS}$ = 4.5 V	0.0112
I <sub>D</sub> (A)	60
Configuration	Single

#### **FEATURES**

- TrenchFET<sup>®</sup> power MOSFET
- AEC-Q101 qualified
- 100 %  $R_q$  and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

N-Channel MOSFET

П

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RoHS COMPLIANT HALOGEN FREE

ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and halogen-free	SQJA82EP (for detailed order number please see <u>www.vishay.com/doc?79771</u> )

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub>	; = 25 °C, unles	s otherwise noted	)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V <sub>DS</sub>	80	v
Gate-Source Voltage		V <sub>GS</sub>	± 20	v
Continuous Drain Current	T <sub>C</sub> = 25 °C ª	1	60	
Continuous Drain Current	T <sub>C</sub> = 125 °C	I <sub>D</sub>	36	
Continuous Source Current (Diode Conduction) <sup>a</sup>	I <sub>S</sub>	60	А	
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	120		
Single Pulse Avalanche Current		I <sub>AS</sub>	35	
Single Pulse Avalanche Energy	L = 0.1 mH	E <sub>AS</sub>	62	mJ
	T <sub>C</sub> = 25 °C	Р	68	w
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 125 °C	P <sub>D</sub>	22	VV VV
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C
Soldering Recommendations (Peak Temperature) d	l, e		260	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount <sup>c</sup>	R <sub>thJA</sub>	68	°C/W
Junction-to-Case (Drain)		R <sub>thJC</sub>	2.2	0/10

#### Notes

a. Package limited

b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %

c. When mounted on 1" square PCB (FR4 material)

d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

S22-0380-Rev. B, 02-May-2022

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SQJA82EP

PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static					•		
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0, I_D = 250 \ \mu A$		80	-	-	V
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$		2.0	2.5	v
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = 80 V	-	-	1	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 80 V, T <sub>J</sub> = 125 °C	-	-	50	μA
		$V_{GS} = 0 V$	V <sub>DS</sub> = 80 V, T <sub>J</sub> = 175 °C	-	-	250	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	30	-	-	Α
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 10 A	-	0.0068	0.0082	
	_	V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 8 A	-	0.0093	0.0112	~
Zero Gate Voltage Drain Current $I_{DSS}$ $V_{GS} = 0 V$ $V_{DS} = V_{DS} = V_{GS} = 0 V$ Dn-State Drain Current a $I_{D(on)}$ $V_{GS} = 0 V$ $V_{DS} = V_{DS} = V_{DS} = 10 V$ Drain-Source On-State Resistance a $R_{DS(on)}$ $V_{GS} = 10 V$ $V_{DS} = 10 V$ Drain-Source On-State Resistance b $g_{fs}$ $V_{DS} = 10 V$ $I_D = V_{GS} = 10 V$ Drain-Source On-State Resistance b $g_{fs}$ $V_{DS} = 15 V$ $V_{DS} = 15 V$ Dynamic b $V_{DS} = 10 V$ $I_D = V_{DS} = 15 V$ $V_{DS} = 15 V$ Dynamic b $V_{GS} = 10 V$ $V_{DS} = 15 V$ $V_{DS} = 15 V$ Dynamic b $V_{GS} = 0 V$ $V_{DS} = 10 V$ $V_{DS} = 10 V$ Catal Gate Charge c $Q_{gg}$ $Q_{gg}$ $V_{GS} = 10 V$ $V_{DS} = 10 V$ Gate -Drain Charge c $Q_{gg}$ $Q_{gg}$ $V_{GS} = 10 V$ $V_{DS} = 10 V$ Gate Resistance $R_g$ $f = 1 N$ $V_{DS} = 10 V$ $V_{DS} = 10 V$ Gate Resistance $R_g$ $f = 1 N$ $V_{DD} = 40 V$ $V_{DS} = 10 V$ Gate Resistance $R_g$ $T_{d(off)}$ $V_{DD} = 40 V$ $V_{DS} = 10 V$ Gate Time c $T_r$ $V_{DD} = 40 V$ $V_{DS} = 10 V$ $V_{DS} = 10 V$ Gate Resistance $R_g$ $T_{S} = 10 V$ $V_{DS} = 10 V$ $V_{DS} = 10 V$ Gate Resistance $R_g$ $T_S = 10 V$ $V_{DS} = 10 V$ $V_{DS} = 10 V$ Gate Resistance $R_g$ $T_S = 10 V$ $V_{DS} = 10 V$ $V_{DS} = 10 V$ Gate Resistance $R_g$ $T_S = 10 V$ $V_$	I <sub>D</sub> = 10 A, T <sub>J</sub> = 125 °C	-	-	0.0134	Ω		
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 10 A, T <sub>J</sub> = 175 °C	-	-	0.0170	
Forward Transconductance b	<b>g</b> fs	V <sub>DS</sub>	= 15 V, I <sub>D</sub> = 10 A	-	53	-	S
Dynamic <sup>b</sup>	-						
Input Capacitance	C <sub>iss</sub>			-	2280	3000	[
Output Capacitance		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 25 V, f = 1 MHz	-	1020	1400	pF
Reverse Transfer Capacitance		-		_	30	45	-
Total Gate Charge <sup>c</sup>				-	40	60	
Gate-Source Charge <sup>c</sup>	Ű.	V <sub>GS</sub> = 10 V	$V_{DS} = 40 \text{ V}, \text{ I}_{D} = 5 \text{ A}$	_	8.5	-	nC
Gate-Drain Charge <sup>c</sup>		-		_	5.5	-	
Gate Resistance			f = 1 MHz	0.2	0.43	0.65	Ω
Turn-On Delay Time <sup>c</sup>				_	14	25	
Rise Time <sup>c</sup>	t <sub>r</sub>	Voo	= 40 V, $R_{\rm L}$ = 8 $\Omega$	_	5	10	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>		$V_{\text{GEN}} = 10 \text{ V}, \text{ R}_{\text{g}} = 1 \Omega$	_	26	40	ns
Fall Time <sup>c</sup>	t <sub>f</sub>	-		-	13	25	1
Source-Drain Diode Ratings and Charac	teristics b					L	
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	120	А
Forward Voltage	V <sub>SD</sub>	IF :	= 10 A, V <sub>GS</sub> = 0	-	0.81	1.2	V
Body diode reverse recovery time	t <sub>rr</sub>	· · ·		-	54	110	ns
Body diode reverse recovery charge	Q <sub>rr</sub>	1		-	80	160	nC
Reverse recovery fall time	ta	I <sub>F</sub> = 10	A, di/dt = 100 A/µs	-	26	-	
Reverse recovery rise time	t <sub>b</sub>	1		-	28	-	ns
Body diode peak reverse recovery current	I <sub>RM(REC)</sub>			_	-2.7	-6	А

Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

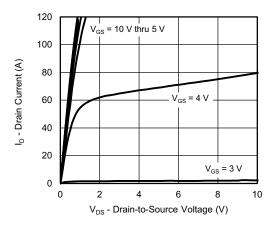
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

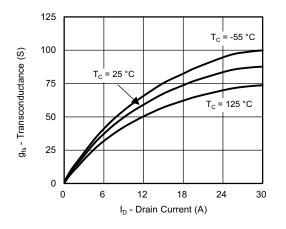
2



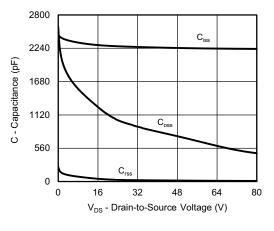
### **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



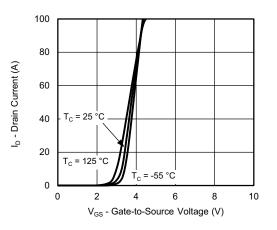
**Output Characteristics** 



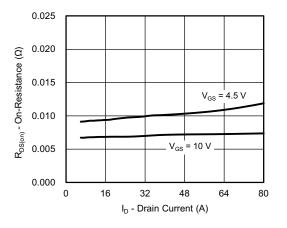
Transconductance



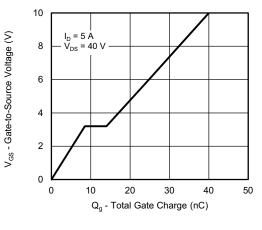
Capacitance



**Transfer Characteristics** 



**On-Resistance vs. Drain Current** 



Gate Charge

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3

Document Number: 75101

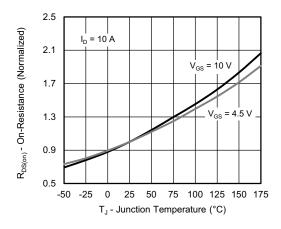
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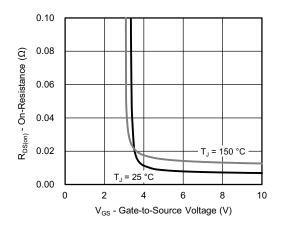
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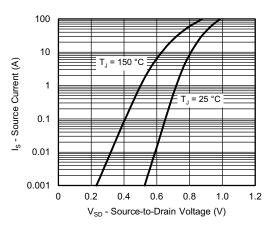
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



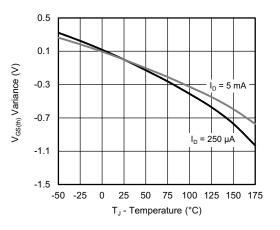
**On-Resistance vs. Junction Temperature** 

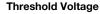


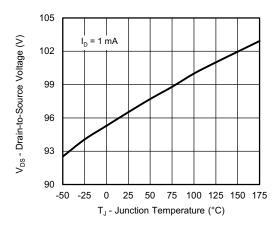
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage







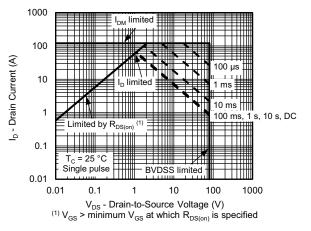
Drain Source Breakdown vs. Junction Temperature

4

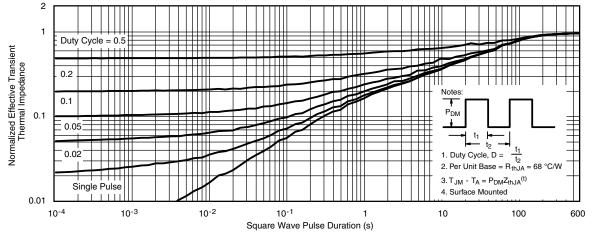
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#### **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



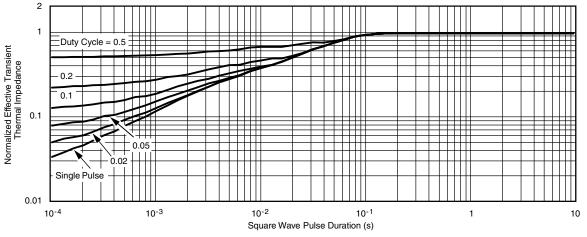
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



#### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

• The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="http://www.vishay.com/ppg?75101">www.vishay.com/ppg?75101</a>.









# **Package Information**



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DIM		MILLIMETERS			INCHES			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.		
А	1.00	1.07	1.14	0.039	0.042	0.045		
A1	0.00	-	0.127	0.00	-	0.005		
b	0.33	0.41	0.48	0.013	0.016	0.019		
b1	0.44	0.51	0.58	0.017	0.020	0.023		
b2	4.80	4.90	5.00	0.189	0.193	0.197		
b3		0.094			0.004			
b4		0.47			0.019			
С	0.20	0.25	0.30	0.008	0.010	0.012		
D	5.00	5.13	5.25	0.197	0.202	0.207		
D1	4.80	4.90	5.00	0.189	0.193	0.197		
D2	3.86	3.96	4.06	0.152	0.156	0.160		
D3	1.63	1.73	1.83	0.064	0.068	0.072		
е		1.27 BSC		0.050 BSC				
E	6.05	6.15	6.25	0.238	0.242	0.246		
E1	4.27	4.37	4.47	0.168	0.172	0.176		
E2	2.75	2.85	2.95	0.108	0.112	0.116		
E3	6.05	6.22	6.40	0.238	0.245	0.252		
F	-	-	0.15	-	-	0.006		
L	0.62	0.72	0.82	0.024	0.028	0.032		
L1	0.92	1.07	1.22	0.036	0.042	0.048		
К		0.51		0.020				
W		0.23		0.009				
W1		0.41		0.016				
W2		2.82		0.111				
W3		2.96		0.117				
θ	0°	-	10°	0°	-	10°		

Note

• Millimeters will govern



#### RECOMMENDED MINIMUM PAD FOR PowerPAK<sup>®</sup> SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)

Revision: 07-Feb-12



Vishay

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